Contents

Preface vii

Conference Organization viii

Sponsors x

I. Process

I-1. Theory

Atomistic processes of surface and interface formation
U. Landman and W.D. Luedtke 1

Theory of electronic excitations on semiconductor surfaces
S.G. Louie 13

Electronic structure of a dimer–adatom–stacking-fault model for the Si(111)7×7 reconstructed surface
S. Ihara, T. Uda and M. Hirao 22

Elementary processes of surface reaction in amorphous silicon film growth
S. Oikawa, S. Ohtsuka and M. Tsuda 29

I-2. Silicon

Statistical properties of atomic-scale Si/SiO_2 interface roughness studied by STM
M. Niwa, H. Iwasaki, Y. Watanabe, I. Sumita, N. Akutsu and Y. Akutsu 39

Microprobe RHEED study of electromigration effect on Si MBE growth
M. Ichikawa and T. Doi 45

New development in the theory of MBE growth of Si: a confrontation with experiment
S. Stoyanov 55

Atomic layer control by electromigration on semiconductor surfaces
H. Yasunaga, N.-J. Wu, S. Yoda, T. Aida and K. Sakamoto 64

The catastrophic phase of electromigration: surface diffusion, island formation, and film thinning
R.W. Vook and C.Y. Chang 71

REM study of surface electromigration of Ge, Au–Cu and Ag on Si(111) surfaces
H. Yamaguchi, Y. Tanishiro and K. Yagi 79

Step structure transformation of Si(001) surface induced by current II
A. Natori, H. Fujimura and M. Fukuda 85

A reflection high-energy electron diffraction study of Si surfaces during gas source MBE growth from disilane
S.M. Mokler, W.K. Liu, N. Ohtani and B.A. Joyce 92

Empirical potential approach to the stability and energetics of thin films and surfaces
S. Das Sarma and K.E. Khor 99

Growth of Si on Au deposited Si(111) surfaces studied by UHV-REM
H. Minoda, Y. Tanishiro, N. Yamamoto and K. Yagi 107

Surface structural changes during the initial growth of Ge on Si(111)7×7
Y. Shinoda, N. Shimizu, H. Hibino, T. Nishioka, C. Heimlich, Y. Kobayashi, S. Ishizawa, K. Sugii and M. Seki 112

Initial growth of Ge films on Si(111)7×7 surfaces by gas source molecular beam epitaxy
N. Ohshima, S. Zaima, Y. Koide, S. Tomioka and Y. Yasuda 120

Chlorine molecular beam scattering study on Si(100)2 × 1: desorption products
K. Karahashi, J. Matsuo and S. Hijiya 126

Simulation of fluorine interaction with a silicon surface
G.V. Gadiyak, Yu.N. Morokov and D.N. Mukhin 131

I-3. Metal on Si

A theoretical study of the growth of metals on silicon
I.P. Batra 136

Structural studies of Al/Si(100) by LEED
K. Murakami, K. Nishikata, M. Yoshimura and A. Kawazu 146

Photoemission studies of Pd initial adsorption on the Si(100)2 × 1 surface at room temperature using synchrotron radiation
S. Kawamoto, K. Saitoh, M. Hirai, M. Kusaka and M. Iwami 152

Adsorption of gallium on Si(110) surfaces
H. Sakama and A. Kawazu 159

Low-energy recoil ion spectroscopy studies of H on Si(111)-7 × 7
F. Shoji and K. Oura 166

The difference of the singlet–triplet conversion efficiency between K/Si and K/Ta surfaces through oxidation process
K. Santo, S. Hongo, S. Saito, T. Urano and T. Kanaji 172

Study of hydrogen adsorption on silicon surfaces by time-of-flight type electron-stimulated desorption spectroscopy (TOF-ESD)
K. Ueda, S. Kodama and A. Takano 178

Hydrogen-induced reconstruction of Si(111)-$\sqrt{3}$-Ag surface studied by TOF-ICISS
T. Kinoshita, Y. Tanaka, K. Sumitomo, F. Shoji, K. Oura and I. Katayama 183

Hydrogen-induced reordering of the Si(111)-$\sqrt{3} \times \sqrt{3}$-Al surface studied by ERDA/LEED
M. Naitoh, H. Ohnishi, Y. Ozaki, F. Shoji and K. Oura 190

Ag thin film growth on hydrogen-terminated Si(100) surface studied by TOF-ICISS
Y. Tanaka, T. Kinoshita, K. Sumitomo, F. Shoji, K. Oura and I. Katayama 195

I-4. III–V compound

Elementary processes in the MBE growth of GaAs
B.A. Joyce, T. Shitara, A. Yoshinaga, D.D. Vvedensky, J.H. Neave and J. Zhang 200

First-principles calculation of the migration energy of a Ga adatom on an As-stabilized GaAs(001) surface
K. Shiraishi 210

A RHEED and RA study of MEE growth
J. Zhang, J.H. Neave, B.A. Joyce, A.G. Taylor, S.R. Armstrong and M.E. Pemble 215

As desorption from GaAs and InAs surfaces studied by improved high-energy electron reflectivity measurements
H. Yamaguchi and Y. Horikoshi 224

Real-time observation of the composition variation due to In–Ga replacements at the GaAs/InAs interface by coaxial impact collision ion scattering spectroscopy
T. Saitoh, A. Hashimoto and M. Tamura 228

Kinetics of MBE growth on flat and stepped surfaces
T. Uchida and K. Wada 234

Trimethylgallium reaction on variously prepared GaAs(100) surfaces studied by mass spectrometry
M. Sasaki, S. Yoshida and Y. Ohki 240

Ab initio molecular orbital study on thermal decomposition of tertiarybutylphosphine
Y.S. Hiraoka, M. Mashita, T. Tada and R. Yoshimura 246

Investigation of growth mechanism of GaAs in molecular beam epitaxy with atomic hydrogen irradiation
T. Sugaya, Y. Okada and M. Kawabe 251

Interfacial chemistry and stability of sulfur-treated GaAs(111)A, 100 and (111)B
T. Scimeca, Y. Muramatsu, M. Oshima, H. Oigawa and Y. Nannichi 256

Anisotropy in surface diffusion of Ga atoms on a Ge(001) plane at the apex of a field-emission tip
T. Honda and T. Okano 260

Early stages of heteroepitaxial growth of ZnSe on GaAs by MOVPE, MOASE and MBE
J.E. Palmer, S. Tohno, Y. Kawaguchi and S. Zembutsu 266

New surface passivation method for GaAs and its effect on the initial growth stage of a heteroepitaxial ZnSe layer
S. Matsumoto, S. Yamaga and A. Yoshikawa 274

I-5. Diamond

Molecular dynamic structure investigations of the adsorption and bonding of C_xH_y-hydrocarbon molecules/radicals on a diamond (111) surface
Th. Frauenheim and P. Blaudeck 281

Diamond growth on carbon-implanted silicon
M. Deguchi, M. Kitabatake, T. Hirao, Y. Mori, J.S. Ma, T. Ito and A. Hiraki 291

Characterizations of metal/CVD diamond interface formation
Y. Mori, N. Eimori, J.S. Ma, T. Ito and A. Hiraki 296

Surface morphology determination of LPCVD homoepitaxial diamond using scanning tunnelling and atomic force microscopy
H.G. Maguire, M. Kamo, H.P. Lang and H.-J. Guntherodt 301

Fabrication of diamond films by a magneto-active plasma CVD using alcohol–hydrogen system
T. Yara, M. Yuasa, J.S. Ma, J. Suzuki, S. Okada and A. Hiraki 308

I-6. Organic materials

STM study of organic thin films of BEDT-TTF iodide
M. Yoshimura, H. Shigekawa, K. Kawabata, Y. Saito and A. Kawazu 317

AFM investigation of microstructures of diacetylene Langmuir–Blodgett films
S. Arisawa, T. Fujii, T. Okane and R. Yamamoto 321

Growth mechanism of thin solid film of long chain compounds on the surface of KCl substrate in molecular level
K. Yase, M. Yamanaka and K. Sato 326

Two-dimensional crystal growth of protein molecules at the lipid/water interface
K. Yase and T. Udaka 330

Effects of organic buffer layers using Langmuir–Blodgett films on TCNQ film growth
K. Kudo, Y. Ueno, S. Kuniyoshi and K. Tanaka 334

Plasma polymerization model in gas-flow type reactor
S. Morita and S.H. Park 338

Structure and formation of polythiophene films studied by scanning tunneling microscopy
S.Z. Dong, Q. Cai, P. Liu and A.R. Zhu 342

Investigation of periodic structures of polyethylene crystal lamellas with STM
Z.Q. Xue, H.J. Gao, W.M. Liu, C. Zhu, Z. Ma and S. Pang 346

II. Characterization

II-1. Electron

Low-energy electron microscopy of surface processes
E. Bauer 350

Characterization of SiO_2/Si(100) interface structure of N_2O-oxynitrided ultrathin SiO_2 films
H. Fukuda, M. Yasuda, T. Iwabuchi and S. Ohno 359

TEM study of Si(111) surfaces
H. Sato, Y. Tanishiro and K. Yagi 367

TEM and SXES study of Ni-silicide/Si interface: crystallographic relationship with the Si substrates
S. Yamauchi, M. Hirai, M. Kusaka, M. Iwami, H. Nakamura, Y. Yokota, A. Akiyama and H. Watabe 372

TEM characterization of the GaP/Si interface grown by MOCVD
T. Soga, Z.K. Jiang, T. Suzuki, T. Jimbo and M. Umeno 380

Cross-sectional TEM observation of the epitaxial Al/Si(111) interface
Y. Yokota, T. Kobayashi, M. Hirai, M. Kusaka, M. Iwami and N. Akiyama 385

Atomic mixing of Bi and Mn by vacuum depositions and structure investigation of its products by high-resolution electron microscopy
K. Yoshida and T. Yamada 391

Direct REM observation of structural processes on clean silicon surfaces during sublimation, phase transition and epitaxy
A.V. Latyshev, A.B. Krasilnikov and A.L. Aseev 397

Developments in RHEED calculations
J.L. Beeby 405

Atomic scale characterization of W surface proposed from FEM images of a tip with and without adsorption
M. Sato 411

ESR study on the nature of oxygen plasma-induced surface radicals of Teflon and corresponding peroxy radical reactivity
M. Kuzuya, S. Kondo, H. Ito and A. Noguchi 416

Fluoride layers and superlattices grown by MBE on Si(111): dynamic RHEED and Sm^{2+} photoluminescence studies
N.S. Sokolov, J.C. Alvarez and N.L. Yakovlev 421

II-2. STM

Probing the chemistry and manipulating surfaces at the atomic scale with the STM
Ph. Avouris and I.-W. Lyo 426

Theoretical calculations of the scanning tunneling microscopy images of the Si(111)$\sqrt{3} \times \sqrt{3}$–Ag surface: effects of the tip shape
S. Watanabe, M. Aono and M. Tsukada 437

Theory of STM images of monolayer graphite on transition-metal surface
K. Kobayashi, Y. Souzu, N. Isshiki and M. Tsukada 443

STM light emission spectroscopy of Au film
S. Ushioda, Y. Uehara and M. Kuwahara 448

Theoretical approach to the microscopic mechanism of light emission from a scanning tunneling microscope
T. Schimizu, K. Kobayashi and M. Tsukada 454

Step bunching structure on vicinal Si(111) surfaces studied by scanning force microscopy
M. Suzuki, Y. Homma, Y. Kudoh and R. Kaneko 460

Atomic scale analyses of HF-treated Si(111) surfaces by STM
Y. Morita, K. Miki and H. Tokumoto 466

Scanning tunneling microscopy of the (331) facets on the vicinal Si(111) surface
H. Tanaka, Y. Watanabe and I. Sumita 474

Step band structures on vicinal Si(111) surfaces created by DC resistive heating
Y. Homma, M. Suzuki and H. Hibino 479

Surface structure and spectroscopy of charge-density wave materials using scanning tunneling microscopy
R.V. Coleman, Z. Dai, W.W. McNairy, C.G. Slough and C. Wang 485

Crystal faces of anhydrite ($CaSO_4$) and their preferential dissolution in aqueous solutions studied with AFM
H. Shindo, M. Kaise, H. Kondoh, C. Nishihara and H. Nozoye 491

II-3. X-ray

Interfacial X-ray oscillations during growth of Pd_2Si on Si(111)
I.K. Robinson, P.J. Eng, P.A. Bennett and B. DeVries 498

Adsorption on a double layer of Ge on Si(111) studied with X-ray standing waves
J. Zegenhagen, J.R. Patel and E. Fontes 505

X-ray standing-wave analysis of the $(NH_4)_2S_x$-treated GaAs(111)B surface
S. Maeyama, M. Sugiyama, M. Oshima, H. Sugahara, H. Oigawa, Y. Nannichi and H. Hashizume 513

X-ray diffraction study of corrugated semiconductor surfaces, quantum wires and quantum boxes
L. Tapfer, G.C. La Rocca, H. Lage, O. Brandt, D. Heitmann and K. Ploog 517

Monolayer superlattices and heterostructures studied by surface-sensitive XAFS
H. Oyanagi 522

Bond length relaxation in ultrathin $Ga_xIn_{1-x}P$ and InP_xAs_{1-x} layers on InP(100)
Y. Kuwahara, H. Oyanagi, Y. Takeda, H. Yamaguchi and M. Aono 529

II-4. Optical

Real time in situ observation of (001)GaAs in OMCVD by reflectance difference spectroscopy
I. Kamiya, D.E. Aspnes, H. Tanaka, L.T. Florez, E. Colas, J.P. Harbison and R. Bhat 534

In-situ optical monitoring of the decomposition process of gaseous sources in metal-organic chemical vapor deposition and atomic layer epitaxy
N. Kobayashi, Y. Kobayashi, Y. Yamauchi and Y. Horikoshi 544

Raman scattering in GaP/AlP short-period superlattices grown by gas source molecular beam epitaxy
R.K. Soni, H. Asahi, S. Emura, T. Watanabe, K. Asami and S. Gonda 553

Determination of some physical parameters from infrared reflectance spectra
W.C. Kok 559

Dislocation of epitaxial CVD diamond and the characterization by Raman spectroscopy
M. Mitsuhashi, S. Karasawa, S. Ohya and F. Togashi 565

II-5. Ion

Studies of surface and interface phenomena by grazing angle neutron reflectometry
M. Mâaza, C. Sella and M. Kâabouchi 573

III. Control

III-1. Silicon

Observation of surface reconstruction and nano-fabrication on silicon under high temperature using a UHV-STM
M. Iwatsuki, S. Kitamura, T. Sato and T. Sueyoshi 580

Synchrotron-radiation-induced growth suppression and initiation in molecular-beam chemical vapor deposition of aluminum
F. Uesugi and I. Nishiyama 587

Silane gas-source atomic layer epitaxy
F. Hirose, M. Suemitsu and N. Miyamoto 592

Improvement of crystallinity of epitaxial $Si_{1-x}Ge_x$ films with SiH_4 treatment in in-situ rapid thermal chemical vapor deposition
K. Ashikaga, M. Ohno, T. Nakamura, H. Fukuda and S. Ohno 597

GeSi–Si strained layer superlattices grown by low-pressure CVD
K. Nakai, Y. Gotoh, M. Ozeki and K. Nakajima 602

Control of rotational twins in a SOI-GaAs film grown on surface modified fluoride/Si(111)
A. Ono, K. Tsutsui and S. Furukawa 608

III-2. III–V compound

Design of atomically abrupt solid interfaces
R.S. Williams 613

Clean and damage-free GaAs surfaces prepared by ultrasonic running deionized water treatment
Y. Hirota, Y. Homma and K. Sugii 619

Gas source MEE growth of InGaAs/InP superlattices
H. Asahi, T. Kohara, R.K. Soni, N. Takeyasu, K. Asami, S. Emura and S. Gonda 625

Evaluation of nucleation and defects in MBE-grown strained InAs/GaAs quantum structures on variously oriented substrates
A. Suzuki, J. Lee, K. Kudo, Y. Makita, A. Yamada and K. Tanaka 631

MBE-grown fluoride/GaAs(111)B heterostructures: control of interfacial barrier by Eu and Sm insulator doping
V.V. Afanas'ev, M.N. Mizerov, S.V. Novikov and N.S. Sokolov 637

III-3. Metal

Surface modification of MoS_2 using an STM
S. Hosoki, S. Hosaka and T. Hasegawa 643

Observation of small metal clusters on graphite surface with scanning tunneling microscopy
J. Shen, C. Zhu, Z. Ma, S. Pang and Z.Q. Xue 648

Monte-Carlo simulation study of the vacuum deposition process
Y. Sasajima, T. Tsukida, S. Ozawa and R. Yamamoto 653

Molecular dynamics simulation of deposition process of ultrafine metal particles on MgO(100) surface
A. Miyamoto, T. Hattori and T. Inui 660

Fundamental processes of the epitaxial growth of silver and gold films
K. Mae, Y. Inoue, K. Kyuno, T. Kaneko and R. Yamamoto 667

Epitaxial Ag film formation on NaCl crystals in Knudsen gases of Ar
I. Ogura, S. Suzuki and S. Nagashima 672

Surface oxidation of Ni–20Cr alloys with small additions of Ce and Si
T. Amano and A. Itoh 677

Weakly bound carbon monoxide at catalytically active sites on Cu(111)/Pd(111) thin films
R.W. Vook and B. Oral 681

Chemisorption of carbon monoxide on Cr(111) studied by XPS, UPS and HREELS
M. Nagoshi and Y. Fukuda 688

On kinetic energy distribution of oxygen ion desorbed from CO-adsorbed Ni(110) by time-of-flight type electron-stimulated desorption
A. Takano and K. Ueda 693

IV. Properties

IV-1. Semiconductors

Atomically controlled surface and interface, and semiconductor device performance
T. Sugano 698

Fabrication process and properties of InGaAs wires having Si interface control layers for removal of Fermi level pinning
H. Fujikura, H. Tomozawa, M. Akazawa and H. Hasegawa 702

Electronic structures of hetero-crystalline semiconductor superlattices
M. Murayama and T. Nakayama 710

Electrical properties of SiN_x/thin-Si-interlayer/GaAs MIS systems ruled by surface superstructures of GaAs and crystallinity of Si interlayers
S. Fujieda, E. Benoit and T. Baba 716

Interface states at lattice-matched and pseudomorphic heterostructures
H. Tomozawa, K. Numata and H. Hasegawa 721

Oxidation of Si(100) surfaces with ultrathin metal overlayers in ozone atmosphere
F. Toda, T. Yamada and H. Abe 729

Schottky barrier formation: Al deposition on GaAs(110)
J. Ortega, R. Rincón, R. Pérez, F.J. García-Vidal and F. Flores 736

IV-2. High T_c and oxide

Atomic layer growth of TiO_2 on silica
E.-L. Lakomaa, S. Haukka and T. Suntola 742

Epitaxial growth of $Bi_4Ti_3O_{12}$ thin films by dual ion-beam sputtering
Y. Ichikawa, H. Adachi, K. Setsune and K. Wasa 749

Observation of the initial growth of semiconductor films on the Bi-based superconducting single crystal by RHEED method. Low temperature reaction of Ge with BSCCO single crystal
K. Yamano, K. Nishimori, H. Tokutaka, S. Kishida and N. Ishihara 754

Control of preferentially oriented crystal growth of titanium nitride. Effects of nitrogen adsorption and ion-beam irradiation in dynamic mixing process
M. Kiuchi, A. Chayahara, Y. Horino, K. Fujii, M. Satou and W. Ensinger 760

Self-limiting behavior of the growth of Al_2O_3 using sequential vapor pulses of TMA and H_2O_2
J.-F. Fan and K. Toyoda 765

Synthesis of MgO/TiO_x superlattices
F. Imai, H. Kuramochi, K. Kunimori, T. Uchijima, H. Kondoh, H. Shindo, C. Nishihara, M. Kaise and H. Nozoye 770

IV-3. Magnetic

Influence of structure on the magnetic anisotropy of Co/Pd (001) epitaxial superlattices
B.N. Engel, M.H. Wiedmann, R.A. Van Leeuwen, C.M. Falco, L. Wu, N. Nakayama and T. Shinjo 776

Microstructural and magnetic characterization of the interfaces in DC triode sputtered metal/carbon and metallic multilayer films
C. Sella, M. Kâabouchi, M. Miloche, M. Mâaza and R. Krishnan 781

MBE growth and magneto-optic properties of magnetic multilayers
C.M. Falco and B.N. Engel 790

Magnetism and magnetoresistance of metallic multilayers
T. Shinjo, H. Yamamoto, T. Anno and T. Okuyama 798

Structural and magnetic properties of Cr/Sb mutilayers
H. Dohnomae, K. Shintaku, N. Nakayama and T. Shinjo 807

Microscopic processes in deposition-concurrent surface segregation
K. Sano and T. Miyagawa 813

Phase-locked epitaxy and structural analysis of Fe/Au(100) artificial superlattices
Y. Suzuki, H. Kikuchi, M. Taninaka, T. Katayama and S. Yoshida 820

Author index 826

Subject index 835